## Abstract Submitted for the MAR06 Meeting of The American Physical Society

Structural and Dielectric Characterization of SrBi<sub>2</sub>Ta<sub>2</sub>O<sub>9</sub> Doped with Gadolinium JORGE MATA, ALEJANDRO DURAN, RAUL ESCAMILLA\*, EDUARDO MARTINEZ, JESUS SIQUEIROS, Centro de Ciencias de la Materia Condensada, UNAM. Apdo. Postal 2681, Ensenada, B.C., Mexico.\*IIM-UNAM, Apartado Postal 70-360, Mexico, D. F. 04510. — The results of the study of polycrystalline samples of SrBi<sub>2</sub>Ta<sub>2</sub>O<sub>9</sub> (SBT) doped with Gd, Sr-vacancies and a Bi-excess are presented. XRD structural characterization using Rietveld refinement revealed that the Gd-doped SBT with Sr-vacancies and Bi-excess  $(Sr_{0.70}?_{0.15}Gd_{0.15}Bi_2Ta_2O_9)$  is single phase. Furthermore, cationic disorder on the  $Bi^{3+}$  and  $Sr^{2+}$  crystallographic sites is promoted by the addition of the  $Gd^{3+}$  ions. Replacement of Gd ions for Sr and vacancies in the SBT structure produces a shift toward lower values of the Curie Temperature (Tc) from 400 to 200 °C in contrast with previous reports in the literature where a notable increase in Tc and the dielectric permittivity are found when the Sr- site is replaced with vacancies. Bi and Gd substitution and the cation vacancies at the Sr site in the  $Sr_{0.70}$ ,  $Sr_{0.15}$ ,  $Sd_{0.15}$ ,  $Bi_2$ ,  $Ta_2O_9$ compound, enhance the structural distortion in the  $TaO_6$  octahedra and leads to a larger ferroelectric spontaneous polarization. Acknowledgments: This work was partially supported by DGAPA-UNAM Project Nº IN100903 and CONACYT No. 47714-F and 40604-F. The authors thank Pedro Casillas, M. Sainz, J. Peralta for their technical assistance.

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